# TEXAS INSTRUMENTS

Data sheet acquired from Harris Semiconductor SCHS192B

#### January 1998 - Revised May 2003

# CD54HCT640, CD74HCT640

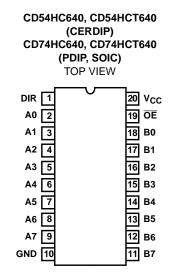
CD54HC640, CD74HC640,

# High-Speed CMOS Logic Octal Three-State Bus Transceiver, Inverting

## Features

- Buffered Inputs
- Three-State Outputs
- Applications in Multiple-Data-Bus Architecture
- Fanout (Over Temperature Range)
  - Standard Outputs..... 10 LSTTL Loads
  - Bus Driver Outputs ..... 15 LSTTL Loads
- Wide Operating Temperature Range . . . -55°C to 125°C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- HC Types
  - 2V to 6V Operation
  - High Noise Immunity: N<sub>IL</sub> = 30%, N<sub>IH</sub> = 30% of V<sub>CC</sub> at V<sub>CC</sub> = 5V
- HCT Types
  - 4.5V to 5.5V Operation
  - Direct LSTTL Input Logic Compatibility, V<sub>IL</sub>= 0.8V (Max), V<sub>IH</sub> = 2V (Min)
  - CMOS Input Compatibility, IJ  $\leq$  1µA at VOL, VOH

### Pinout



## Description

The 'HC640 and 'HCT640 silicon-gate CMOS three-state bidirectional inverting and non-inverting buffers are intended for two-way asynchronous communication between data buses. They have high drive current outputs which enable high-speed operation when driving large bus capacitances. These circuits possess the low power dissipation of CMOS circuits, and have speeds comparable to low power Schottky TTL circuits. They can drive 15 LSTTL loads. The 'HC640 and 'HCT640 are inverting buffers.

The direction of data flow (A to B, B to A) is controlled by the DIR input.

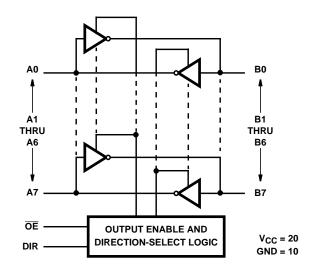
Outputs are enabled by a low on the Output Enable input  $(\overline{OE})$ ; a high  $\overline{OE}$  puts these devices in the high impedance mode.

# **Ordering Information**

| PART NUMBER   | TEMP. RANGE<br>( <sup>O</sup> C) | PACKAGE      |
|---------------|----------------------------------|--------------|
| CD54HC640F3A  | -55 to 125                       | 20 Ld CERDIP |
| CD54HCT640F3A | -55 to 125                       | 20 Ld CERDIP |
| CD74HC640E    | -55 to 125                       | 20 Ld PDIP   |
| CD74HC640M    | -55 to 125                       | 20 Ld SOIC   |
| CD74HCT640E   | -55 to 125                       | 20 Ld PDIP   |
| CD74HCT640M   | -55 to 125                       | 20 Ld SOIC   |

CAUTION: These devices are sensitive to electrostatic discharge. Users should follow proper IC Handling Procedures. Copyright © 2003, Texas Instruments Incorporated

# Functional Diagram



#### TRUTH TABLE

| CONTRO | L INPUTS | DATA PORT STATUS |                |  |  |  |
|--------|----------|------------------|----------------|--|--|--|
| ŌĒ     | DIR      | A <sub>n</sub>   | B <sub>n</sub> |  |  |  |
| L      | L        | ō                | I              |  |  |  |
| н      | Н        | Z                | Z              |  |  |  |
| н      | L        | Z                | Z              |  |  |  |
| L      | Н        | I                | ō              |  |  |  |

To prevent excess currents in the High-Z modes all I/O terminals should be terminated with  $1k\Omega$  to  $1M\Omega$  resistors.

H = High Level

L = Low Level

I = Input

 $\overline{O}$  = Output (Inversion of Input Level)

Z = High Impedance

## **Absolute Maximum Ratings**

| DC Supply Voltage, V <sub>CC</sub> 0.5V to 7V<br>DC Input Diode Current, I <sub>IK</sub> |
|--|
| For $V_{l} < -0.5V$ or $V_{l} > V_{CC} + 0.5V$ ±20mA                                     |
| DC Output Diode Current, IOK   |
| For $V_0 < -0.5V$ or $V_0 > V_{CC} + 0.5V$   |
| DC Drain Current, per Output, I <sub>O</sub>   |
| For -0.5V < V <sub>O</sub> < V <sub>CC</sub> + 0.5V±35mA                                 |
| DC Output Source or Sink Current per Output Pin, IO                                      |
| For $V_0 > -0.5V$ or $V_0 < V_{CC} + 0.5V$ ±25mA   |
| DC V <sub>CC</sub> or Ground Current, I <sub>CC</sub> ±50mA                              |
|  |

## **Operating Conditions**

| Temperature Range, T <sub>A</sub>            |
|--|
| Supply Voltage Range, V <sub>CC</sub>        |
| HC Types                                     |
| HCT Types4.5V to 5.5V                        |
| DC Input or Output Voltage, VI, VO 0V to VCC |
| Input Rise and Fall Time                     |
| 2V   |
| 4.5V 500ns (Max)                             |
| 6V   |
|  |

## **Thermal Information**

| Thermal Resistance (Typical, Note 1)     | θ <sub>JA</sub> ( <sup>o</sup> C/W)      |
|--|--|
| E (PDIP) Package                         | . 69                                     |
| M (SOIC) Package                         | . 58                                     |
| Maximum Junction Temperature             | 150 <sup>0</sup> C                       |
| Maximum Storage Temperature Range        | -65 <sup>o</sup> C to 150 <sup>o</sup> C |
| Maximum Lead Temperature (Soldering 10s) |  |
| (SOIC - Lead Tips Only)                  |  |

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

#### NOTE:

1. The package thermal impedance is calculated in accordance with JESD 51-7.

# **DC Electrical Specifications**

|  |                 | TE:<br>CONDI                       |                     | v <sub>cc</sub> | 25 <sup>0</sup> C |     |      | -40°C TO 85°C |      | -55 <sup>°</sup> C TO 125 <sup>°</sup> C |      |       |
|--|-----------------|------------------------------------|---------------------|-----------------|-------------------|-----|------|---------------|------|--|------|-------|
| PARAMETER                                  | SYMBOL          | V <sub>I</sub> (V)                 | I <sub>O</sub> (mA) | (Ÿ)             | MIN               | TYP | MAX  | MIN           | MAX  | MIN                                      | MAX  | UNITS |
| HC TYPES                                   |                 | -                                  |                     |                 |                   |     | _    | _             |      | _  |      |       |
| High Level Input                           | VIH             | -                                  | -                   | 2               | 1.5               | -   | -    | 1.5           | -    | 1.5                                      | -    | V     |
| Voltage                                    |                 |                                    |                     | 4.5             | 3.15              | -   | -    | 3.15          | -    | 3.15                                     | -    | V     |
|  |                 |                                    |                     | 6               | 4.2               | -   | -    | 4.2           | -    | 4.2                                      | -    | V     |
| Low Level Input                            | VIL             | -                                  | -                   | 2               | -                 | -   | 0.5  | -             | 0.5  | -  | 0.5  | V     |
| Voltage                                    |                 |                                    |                     | 4.5             | -                 | -   | 1.35 | -             | 1.35 | -  | 1.35 | V     |
|  |                 |                                    |                     | 6               | -                 | -   | 1.8  | -             | 1.8  | -  | 1.8  | V     |
| High Level Output<br>Voltage<br>CMOS Loads | V <sub>OH</sub> | V <sub>IH</sub> or V <sub>IL</sub> | -0.02               | 2               | 1.9               | -   | -    | 1.9           | -    | 1.9                                      | -    | V     |
|  |                 |                                    | -0.02               | 4.5             | 4.4               | -   | -    | 4.4           | -    | 4.4                                      | -    | V     |
|  |                 |                                    | -0.02               | 6               | 5.9               | -   | -    | 5.9           | -    | 5.9                                      | -    | V     |
| High Level Output                          | 1               |                                    | -                   | -               | -                 | -   | -    | -             | -    | -  | -    | V     |
| Voltage<br>TTL Loads                       |                 |                                    | -6                  | 4.5             | 3.98              | -   | -    | 3.84          | -    | 3.7                                      | -    | V     |
|  |                 |                                    | -7.8                | 6               | 5.48              | -   | -    | 5.34          | -    | 5.2                                      | -    | V     |
| Low Level Output                           | V <sub>OL</sub> | V <sub>IH</sub> or V <sub>IL</sub> | 0.02                | 2               | -                 | -   | 0.1  | -             | 0.1  | -  | 0.1  | V     |
| Voltage<br>CMOS Loads                      |                 |                                    | 0.02                | 4.5             | -                 | -   | 0.1  | -             | 0.1  | -  | 0.1  | V     |
|  |                 |                                    | 0.02                | 6               | -                 | -   | 0.1  | -             | 0.1  | -  | 0.1  | V     |
| Low Level Output                           | 7               |                                    | -                   | -               | -                 | -   | -    | -             | -    | -  | -    | V     |
| Voltage<br>TTL Loads                       |                 |                                    | 6                   | 4.5             | -                 | -   | 0.26 | -             | 0.33 | -  | 0.4  | V     |
|  |                 |                                    | 7.8                 | 6               | -                 | -   | 0.26 | -             | 0.33 | -  | 0.4  | V     |
| Input Leakage<br>Current                   | lı              | V <sub>CC</sub> or<br>GND          | -                   | 6               | -                 | -   | ±0.1 | -             | ±1   | -  | ±1   | μA    |

# CD54HC640, CD74HC640, CD54HCT640, CD74HCT640

## DC Electrical Specifications (Continued)

|  |                              | TEST<br>CONDITIONS                 |   | v <sub>cc</sub> | 25°C |     |      | -40°C TO 85°C |      | -55°C TO 125°C |     |       |  |
|--|------------------------------|------------------------------------|---|-----------------|------|-----|------|---------------|------|----------------|-----|-------|--|
| PARAMETER  | SYMBOL                       | V <sub>I</sub> (V)                 | I <sub>O</sub> (mA)                           | (V)             | MIN  | TYP | MAX  | MIN           | MAX  | MIN            | MAX | UNITS |  |
| Quiescent Device<br>Current  | Icc                          | V <sub>CC</sub> or<br>GND          | 0   | 6               | -    | -   | 8    | -             | 80   | -              | 160 | μA    |  |
| Three-State Leakage<br>Current                                       | I <sub>OZ</sub>              | V <sub>IL</sub> or V <sub>IH</sub> | V <sub>O</sub> =<br>V <sub>CC</sub> or<br>GND | 6               | -    | -   | ±0.5 | -             | ±5   | -              | ±10 | μΑ    |  |
| HCT TYPES  |                              |                                    |   |                 |      |     |      |               |      |                |     |       |  |
| High Level Input<br>Voltage  | VIH                          | -                                  | -   | 4.5 to<br>5.5   | 2    | -   | -    | 2             | -    | 2              | -   | V     |  |
| Low Level Input<br>Voltage   | V <sub>IL</sub>              | -                                  | -   | 4.5 to<br>5.5   | -    | -   | 0.8  | -             | 0.8  | -              | 0.8 | V     |  |
| High Level Output<br>Voltage<br>CMOS Loads                           | V <sub>OH</sub>              | V <sub>IH</sub> or V <sub>IL</sub> | -0.02   | 4.5             | 4.4  | -   | -    | 4.4           | -    | 4.4            | -   | V     |  |
| High Level Output<br>Voltage<br>TTL Loads                            |                              |                                    | -6  | 4.5             | 3.98 | -   | -    | 3.84          | -    | 3.7            | -   | V     |  |
| Low Level Output<br>Voltage<br>CMOS Loads                            | V <sub>OL</sub>              | V <sub>IH</sub> or V <sub>IL</sub> | 0.02  | 4.5             | -    | -   | 0.1  | -             | 0.1  | -              | 0.1 | V     |  |
| Low Level Output<br>Voltage<br>TTL Loads                             |                              |                                    | 6   | 4.5             | -    | -   | 0.26 | -             | 0.33 | -              | 0.4 | V     |  |
| Input Leakage<br>Current   | lı                           | V <sub>CC</sub> and<br>GND         | 0   | 5.5             | -    | -   | ±0.1 | -             | ±1   | -              | ±1  | μA    |  |
| Quiescent Device<br>Current  | Icc                          | V <sub>CC</sub> or<br>GND          | 0   | 5.5             | -    | -   | 8    | -             | 80   | -              | 160 | μA    |  |
| Three-State Leakage<br>Current                                       | I <sub>OZ</sub>              | V <sub>IL</sub> or V <sub>IH</sub> | V <sub>O</sub> =<br>V <sub>CC</sub> or<br>GND | 5.5             | -    | -   | ±0.5 | -             | ±5   | -              | ±10 | μA    |  |
| Additional Quiescent<br>Device Current Per<br>Input Pin: 1 Unit Load | ΔI <sub>CC</sub><br>(Note 2) | V <sub>CC</sub><br>-2.1            | -   | 4.5 to<br>5.5   | -    | 100 | 360  | -             | 450  | -              | 490 | μΑ    |  |

NOTE:

2. For dual-supply systems theoretical worst case (V<sub>I</sub> = 2.4V, V<sub>CC</sub> = 5.5V) specification is 1.8mA.

## **HCT Input Loading Table**

| INPUT | UNIT LOADS |
|-------|------------|
| DIR   | 0.9        |
| OE, A | 1.5        |
| В     | 1.5        |

NOTE: Unit Load is  $\Delta I_{CC}$  limit specified in DC Electrical Table, e.g., 360µA max at 25°C.

# CD54HC640, CD74HC640, CD54HCT640, CD74HCT640

|   |                                     | TEST                  |                     |     | 25 <sup>0</sup> C |     |     | С ТО<br>°С |     | С ТО<br>5°С |          |
|---|-------------------------------------|-----------------------|---------------------|-----|-------------------|-----|-----|------------|-----|-------------|----------|
| PARAMETER                                     | SYMBOL                              | CONDITIONS            | V <sub>CC</sub> (V) | MIN | TYP               | MAX | MIN | MAX        | MIN | MAX         |          |
| HC TYPES                                      |                                     |                       |                     |     |                   |     |     |            |     |             |          |
| Propagation Delay                             | t <sub>PHL</sub> , t <sub>PLH</sub> | $C_L = 50 pF$         |                     |     |                   |     |     |            |     |             | Γ        |
| A to $\overline{B}$<br>B to $\overline{A}$    |                                     |                       | 2                   | -   | -                 | 90  | -   | 115        | -   | 135         | ns       |
|   |                                     |                       | 4.5                 | -   | -                 | 18  | -   | 23         | -   | 27          | ns       |
|   |                                     | C <sub>L</sub> = 15pF | 5                   | -   | 7                 | -   | -   | -          | -   | -           | ns       |
|   |                                     | C <sub>L</sub> = 50pF | 6                   | -   | -                 | 15  | -   | 20         | -   | 23          | ns       |
| Output High-Z<br>To High Level,               | <sup>t</sup> PHL, <sup>t</sup> PLH  | $C_L = 50 pF$         | 2                   | -   | -                 | 150 | -   | 190        | -   | 225         | ns       |
| To Low Level                                  |                                     |                       | 4.5                 | -   | -                 | 30  | -   | 38         | -   | 45          | ns       |
|   |                                     | C <sub>L</sub> = 15pF | 5                   | -   | 12                | -   | -   | -          | -   | -           | ns       |
|   |                                     | $C_L = 50 pF$         | 6                   | -   | -                 | 26  | -   | 33         | -   | 38          | ns       |
| Output High Level                             | t <sub>PHZ</sub> , t <sub>PLZ</sub> | C <sub>L</sub> = 50pF | 2                   | -   | -                 | 150 | -   | 190        | -   | 225         | ns       |
| Output Low Level to High Z                    |                                     |                       | 4.5                 | -   | -                 | 30  | -   | 38         | -   | 45          | ns       |
|   |                                     | C <sub>L</sub> = 15pF | 5                   | -   | 12                | -   | -   | -          | -   | -           | ns       |
|   |                                     | C <sub>L</sub> = 50pF | 6                   | -   | -                 | 26  | -   | 33         | -   | 38          | ns       |
| Output Transition Time                        | t <sub>THL</sub> , t <sub>TLH</sub> | C <sub>L</sub> = 50pF | 2                   | -   | -                 | 60  | -   | 75         | -   | 90          | ns       |
|   |                                     |                       | 4.5                 | -   | -                 | 12  | -   | 15         | -   | 18          | ns       |
|   |                                     |                       | 6                   | -   | -                 | 10  | -   | 13         | -   | 15          | ns       |
| Input Capacitance                             | C <sub>IN</sub>                     | C <sub>L</sub> = 50pF | -                   | 10  | -                 | 10  | -   | 10         | -   | 10          | pF       |
| Three-State Output<br>Capacitance             | CO                                  | -                     | -                   | -   | -                 | 20  | -   | 20         | -   | 20          | pF       |
| Power Dissipation Capacitance<br>(Notes 3, 4) | C <sub>PD</sub>                     | -                     | 5                   | -   | 38                | -   | -   | -          | -   | -           | pF       |
| HCT TYPES                                     |                                     |                       | <u>.</u>            |     |                   |     |     |            |     |             | <u>.</u> |
| Propagation Delay                             |                                     |                       |                     |     |                   |     |     |            |     |             |          |
| A to $\overline{B}$<br>B to $\overline{A}$    | <sup>t</sup> PHL, <sup>t</sup> PLH  | $C_L = 50 pF$         | 4.5                 | -   | -                 | 22  | -   | 28         | -   | 33          | ns       |
| D IO A  |                                     | C <sub>L</sub> = 15pF | 5                   | -   | 9                 | -   | -   | -          | -   | -           | ns       |
| Output High-Z                                 | t <sub>PHL,</sub> t <sub>PLH</sub>  | $C_L = 50 pF$         | 4.5                 | -   | -                 | 30  | -   | 38         | -   | 45          | ns       |
| To High Level,<br>To Low Level                |                                     | C <sub>L</sub> = 15pF | 5                   | -   | 12                | -   | -   | -          | -   | -           | ns       |
| Output High Level                             | t <sub>PHZ</sub> , t <sub>PLZ</sub> | C <sub>L</sub> = 50pF | 4.5                 | -   | -                 | 30  | -   | 38         | -   | 45          | ns       |
| Output Low Level to High Z                    |                                     | C <sub>L</sub> = 15pF | 5                   | -   | 12                | - 1 | -   | -          | -   | -           | ns       |
| Output Transition Time                        | t <sub>THL</sub> , t <sub>TLH</sub> | $C_L = 50 pF$         | 4.5                 | -   | -                 | 12  | -   | 15         | -   | 18          | ns       |
| Input Capacitance                             | C <sub>IN</sub>                     | C <sub>L</sub> = 50pF | -                   | 10  | -                 | 10  | -   | 10         | -   | 10          | pF       |
| Three-State Output<br>Capacitance             | CO                                  | -                     | -                   | -   | -                 | 20  | -   | 20         | -   | 20          | pF       |
| Power Dissipation Capacitance (Notes 3, 4)    | C <sub>PD</sub>                     | -                     | 5                   | -   | 41                | -   | -   | -          | -   | -           | pF       |

NOTES:

3.  $C_{PD}$  is used to determine the dynamic power consumption, per channel. 4.  $P_D = V_{CC}^2 f_i (C_{PD} + C_L)$  where  $f_i$  = Input Frequency,  $C_L$  = Output Load Capacitance,  $V_{CC}$  = Supply Voltage.

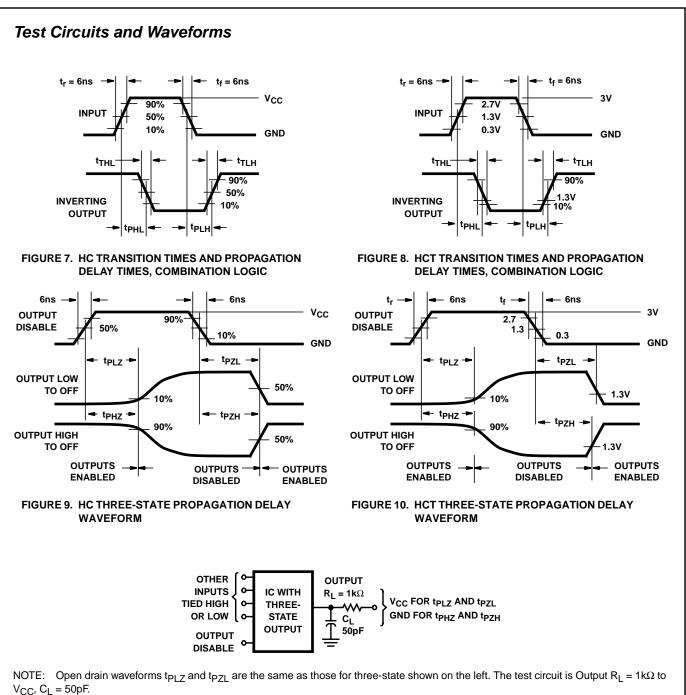


FIGURE 11. HC AND HCT THREE-STATE PROPAGATION DELAY TEST CIRCUIT



25-Sep-2013

# **PACKAGING INFORMATION**

| Orderable Device | Status | Package Type | -       | Pins | Package | Eco Plan                   | Lead/Ball Finish | MSL Peak Temp      | Op Temp (°C) | Device Marking                  | Samples |
|------------------|--------|--------------|---------|------|---------|----------------------------|------------------|--------------------|--------------|---------------------------------|---------|
|                  | (1)    |              | Drawing |      | Qty     | (2)                        |                  | (3)                |              | (4/5)                           |         |
| 5962-8974001RA   | ACTIVE | CDIP         | J       | 20   | 1       | TBD                        | A42              | N / A for Pkg Type | -55 to 125   | 5962-8974001RA<br>CD54HCT640F3A | Samples |
| CD54HC640F3A     | ACTIVE | CDIP         | J       | 20   | 1       | TBD                        | A42              | N / A for Pkg Type | -55 to 125   | 5962-8780901RA<br>CD54HC640F3A  | Samples |
| CD54HCT640F3A    | ACTIVE | CDIP         | J       | 20   | 1       | TBD                        | A42              | N / A for Pkg Type | -55 to 125   | 5962-8974001RA<br>CD54HCT640F3A | Samples |
| CD74HC640E       | ACTIVE | PDIP         | Ν       | 20   | 20      | Pb-Free<br>(RoHS)          | CU NIPDAU        | N / A for Pkg Type | -55 to 125   | CD74HC640E                      | Samples |
| CD74HC640EE4     | ACTIVE | PDIP         | Ν       | 20   | 20      | Pb-Free<br>(RoHS)          | CU NIPDAU        | N / A for Pkg Type | -55 to 125   | CD74HC640E                      | Samples |
| CD74HC640M       | ACTIVE | SOIC         | DW      | 20   | 25      | Green (RoHS<br>& no Sb/Br) | CU NIPDAU        | Level-1-260C-UNLIM | -55 to 125   | HC640M                          | Samples |
| CD74HC640ME4     | ACTIVE | SOIC         | DW      | 20   | 25      | Green (RoHS<br>& no Sb/Br) | CU NIPDAU        | Level-1-260C-UNLIM | -55 to 125   | HC640M                          | Samples |
| CD74HC640MG4     | ACTIVE | SOIC         | DW      | 20   | 25      | Green (RoHS<br>& no Sb/Br) | CU NIPDAU        | Level-1-260C-UNLIM | -55 to 125   | HC640M                          | Samples |
| CD74HCT640E      | ACTIVE | PDIP         | N       | 20   | 20      | Pb-Free<br>(RoHS)          | CU NIPDAU        | N / A for Pkg Type | -55 to 125   | CD74HCT640E                     | Samples |
| CD74HCT640EE4    | ACTIVE | PDIP         | Ν       | 20   | 20      | Pb-Free<br>(RoHS)          | CU NIPDAU        | N / A for Pkg Type | -55 to 125   | CD74HCT640E                     | Samples |
| CD74HCT640M      | ACTIVE | SOIC         | DW      | 20   | 25      | Green (RoHS<br>& no Sb/Br) | CU NIPDAU        | Level-1-260C-UNLIM | -55 to 125   | HCT640M                         | Samples |
| CD74HCT640ME4    | ACTIVE | SOIC         | DW      | 20   | 25      | Green (RoHS<br>& no Sb/Br) | CU NIPDAU        | Level-1-260C-UNLIM | -55 to 125   | HCT640M                         | Samples |
| CD74HCT640MG4    | ACTIVE | SOIC         | DW      | 20   | 25      | Green (RoHS<br>& no Sb/Br) | CU NIPDAU        | Level-1-260C-UNLIM | -55 to 125   | HCT640M                         | Samples |

<sup>(1)</sup> The marketing status values are defined as follows: **ACTIVE:** Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.



25-Sep-2013

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

**TBD:** The Pb-Free/Green conversion plan has not been defined.

**Pb-Free (RoHS):** TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes. **Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

<sup>(3)</sup> MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

<sup>(4)</sup> There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(<sup>5)</sup> Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

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#### OTHER QUALIFIED VERSIONS OF CD54HC640, CD54HCT640, CD74HC640, CD74HCT640 :

• Catalog: CD74HC640, CD74HCT640

• Military: CD54HC640, CD54HCT640

NOTE: Qualified Version Definitions:

- Catalog TI's standard catalog product
- Military QML certified for Military and Defense Applications

J (R-GDIP-T\*\*) 14 LEADS SHOWN

CERAMIC DUAL IN-LINE PACKAGE



NOTES: A. All linear dimensions are in inches (millimeters).

- B. This drawing is subject to change without notice.
- C. This package is hermetically sealed with a ceramic lid using glass frit.
- D. Index point is provided on cap for terminal identification only on press ceramic glass frit seal only.
- E. Falls within MIL STD 1835 GDIP1-T14, GDIP1-T16, GDIP1-T18 and GDIP1-T20.

# N (R-PDIP-T\*\*)

PLASTIC DUAL-IN-LINE PACKAGE

16 PINS SHOWN



NOTES:

- A. All linear dimensions are in inches (millimeters).B. This drawing is subject to change without notice.
- Falls within JEDEC MS-001, except 18 and 20 pin minimum body length (Dim A).
- $\triangle$  The 20 pin end lead shoulder width is a vendor option, either half or full width.



DW (R-PDSO-G20)

PLASTIC SMALL OUTLINE



NOTES: A. All linear dimensions are in inches (millimeters). Dimensioning and tolerancing per ASME Y14.5M-1994.

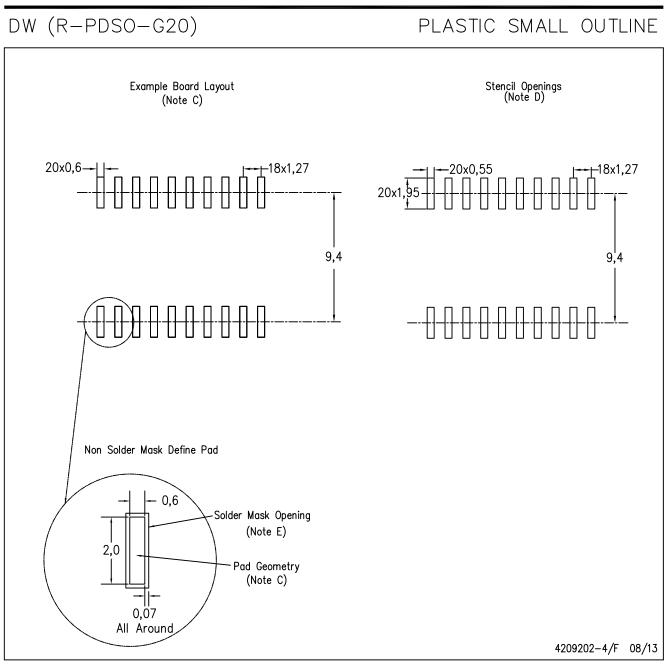
B. This drawing is subject to change without notice.

C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15).

D. Falls within JEDEC MS-013 variation AC.



# LAND PATTERN DATA



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Refer to IPC7351 for alternate board design.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



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